Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- · Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-40	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{sp} = 25 °C		-	-	-14	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C		-	-	15	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -6 A; T_j = 25 °C		-	30	43	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	15/	D -
2	D	drain	7 7	(1: 47)
3	G	gate	2 5	G UP
4	S	source	3 8 4	s
5	D	drain	Transparent top view	017aaa094
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK6D43-40P	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK6D43-40P	4D

40 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-40	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{sp} = 25 °C		-	-14	Α
		V _{GS} = -10 V; T _{sp} = 100 °C		-	-8.9	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-6	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-56	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C		-	15	W
		T _{amb} = 25 °C	[1]	-	2.3	W
T _j	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-dra	in diode					
I _S	source current	T _{sp} = 25 °C		-	-14	Α
		T _{amb} = 25 °C	[1]	-	-2.3	Α
I _{SM}	peak source current	single pulse; t_p = 10 μ s; T_{sp} = 25 °C		-	-56	Α
ESD maxim	num rating		,			
V_{ESD}	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche	ruggedness			'		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -1.4 A; DUT in avalanche (unclamped)		-	29.7	mJ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

^[2] Measured between all pins.

40 V, P-channel Trench MOSFET

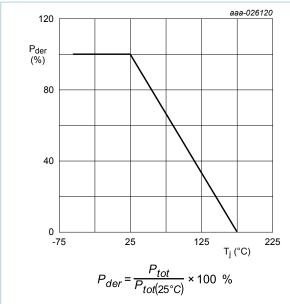


Fig. 1. Normalized total power dissipation as a function of junction temperature

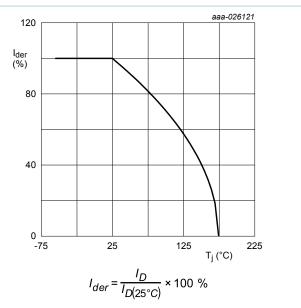


Fig. 2. Normalized continuous drain current as a function of junction temperature

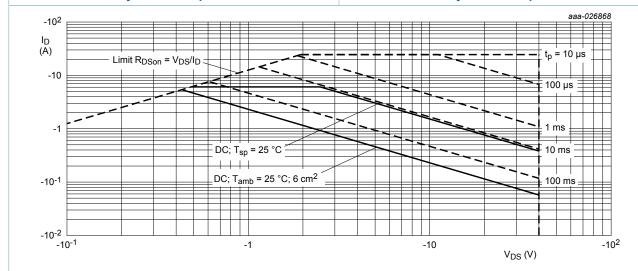


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

40 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	57	66	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	6	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

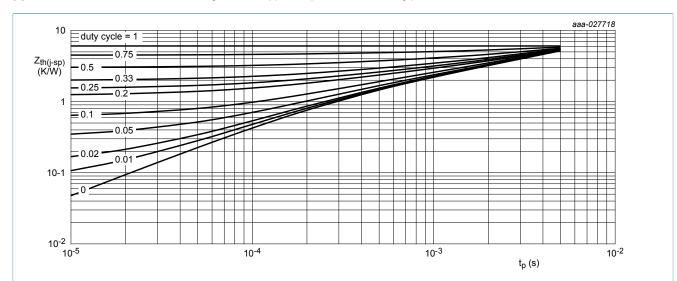


Fig. 4. Transient thermal impedance from junction to solder point as a function of pulse duration; typical values

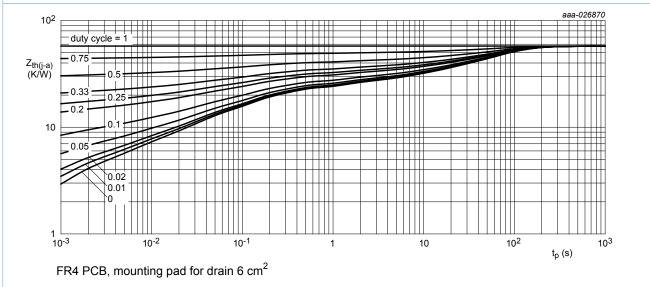


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

40 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					,
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-40	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$	-1.4	-2	-2.7	V
I _{DSS}	drain leakage current	$V_{DS} = -40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-1	μA
		V _{DS} = -40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	-500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -6 A; T_j = 25 °C	-	30	43	mΩ
	resistance	V_{GS} = -10 V; I_D = -6 A; T_j = 175 °C	-	57	81	mΩ
		V_{GS} = -4.5 V; I_D = -4.1 A; T_j = 25 °C	-	45	70	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -5 A; T_j = 25 °C	-	33	-	S
R_G	gate resistance	f = 1 MHz	-	6	-	Ω
Dynamic c	haracteristics		,			
Q _{G(tot)}	total gate charge	V_{DS} = -20 V; I_{D} = -5 A; V_{GS} = -10 V;	-	24	36	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	4.2	-	nC
Q_{GD}	gate-drain charge		-	5.4	-	nC
C _{iss}	input capacitance	V _{DS} = -20 V; f = 1 MHz; V _{GS} = 0 V;	-	1260	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	106	-	pF
C _{rss}	reverse transfer capacitance		-	91	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -20 V; I_D = -5 A; V_{GS} = -10 V;	-	9	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	23	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
t _f	fall time		-	14	-	ns
Source-dra	in diode		'	,		,
V_{SD}	source-drain voltage	$I_S = -2.3 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
t _{rr}	reverse recovery time	$I_S = -2.3 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	15.6	-	ns
		$V_{GS} = 0 \text{ V}; V_{DS} = -20 \text{ V}; T_i = 25 ^{\circ}\text{C}$		_		_

40 V, P-channel Trench MOSFET

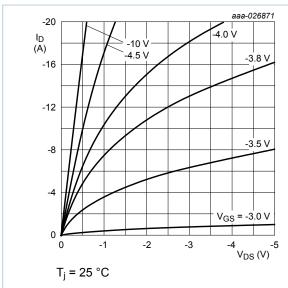


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

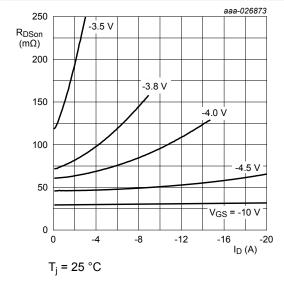


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

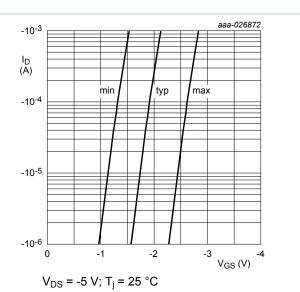


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

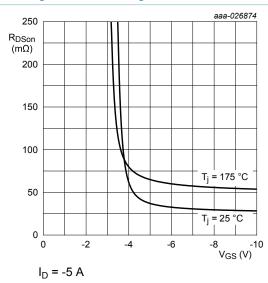


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

40 V, P-channel Trench MOSFET

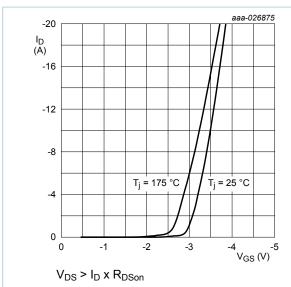


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

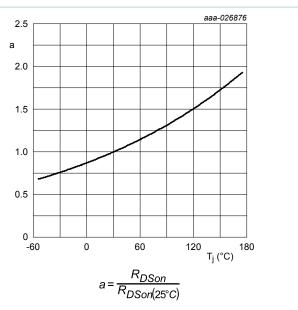


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

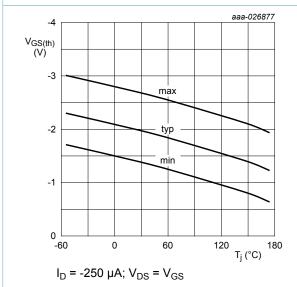


Fig. 12. Gate-source threshold voltage as a function of junction temperature

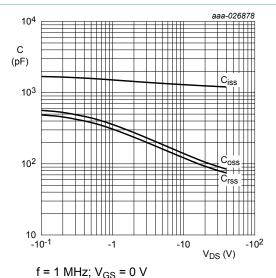


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

40 V, P-channel Trench MOSFET

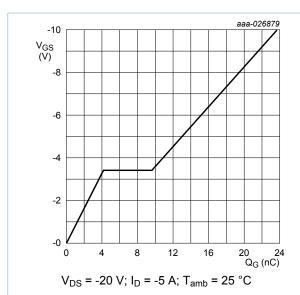


Fig. 14. Gate-source voltage as a function of gate charge; typical values

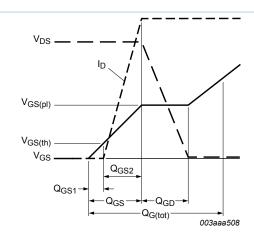


Fig. 15. Gate charge waveform definitions

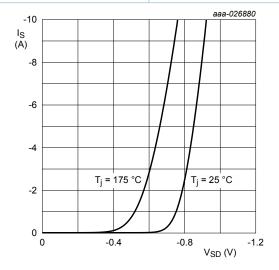
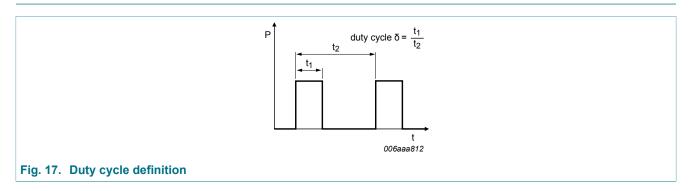


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

40 V, P-channel Trench MOSFET

11. Test information

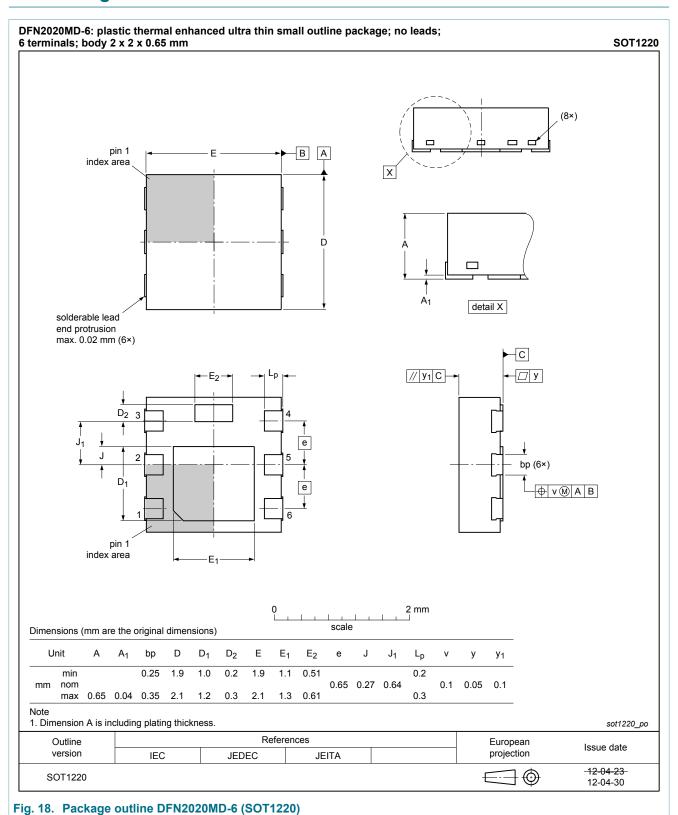


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

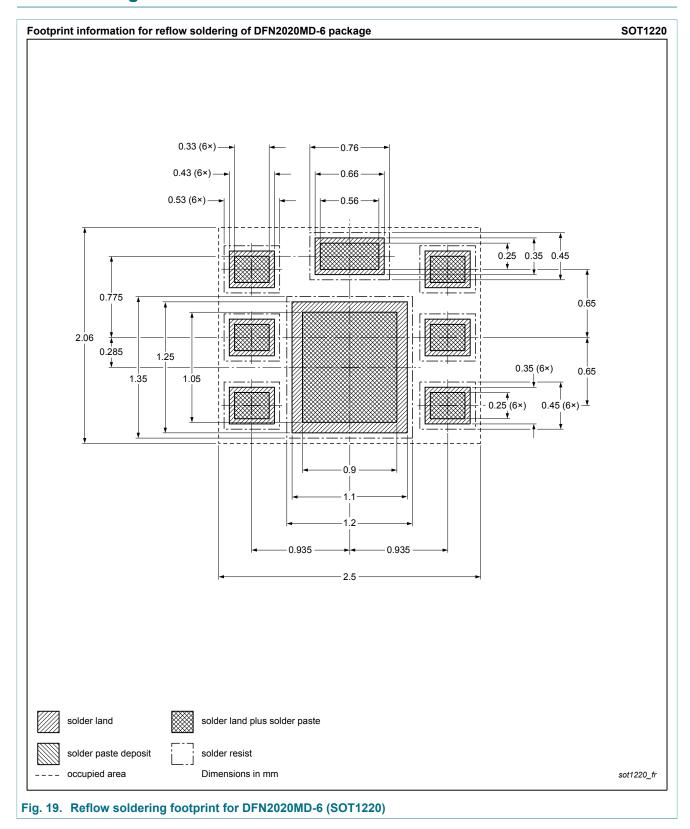
40 V, P-channel Trench MOSFET

12. Package outline



40 V, P-channel Trench MOSFET

13. Soldering



40 V, P-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID Release date		Data sheet status	Change notice	Supersedes				
BUK6D43-40P v.2	20171220	Product data sheet	-	BUK6D43-40P v.1				
Modifications:	Characteristics, temperature condition changed for drain leakage current.							
BUK6D43-40P v.1	20171214	Product data sheet	-	-				

40 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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40 V, P-channel Trench MOSFET

16. Contents

1. Gene	eral description	1
2. Featu	ures and benefits	1
3. Appl	ications	1
4. Quic	k reference data	1
5. Pinni	ing information	2
6. Orde	ring information	2
7. Mark	ing	2
8. Limit	ting values	3
9. Ther	mal characteristics	5
10. Cha	racteristics	6
11. Tes	t information	10
12. Pac	kage outline	11
13. Sol	dering	12
14. Rev	rision history	13
15. Leg	al information	14

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15 / 15

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